

### **ABSTRACT OF THE DISCLOSURE**

1           A semiconductor device including an IGFET (insulated gate field effect transistor)  
2   (30) is disclosed. IGFET (30) may include a source/drain area (15) having an impurity  
3   concentration distribution that may be formed shallower at a higher concentration than the  
4   impurity concentration distribution in another source/drain area (7). A gate oxide film may  
5   include a first gate oxide film (5) adjacent to source/drain area (7) and a second gate oxide  
6   film (12) adjacent to source drain area (15). Second gate oxide film (12) may be thinner than  
7   first gate oxide film (5). An impurity concentration distribution of a second channel impurity  
8   area (11) under second gate oxide film (12) may be at a higher concentration than an  
9   impurity concentration distribution of a first channel impurity area (9) under first gate oxide  
10   film (5). In this way, an electric field at a PN junction of source/drain area (7) may be  
11   reduced.